



CYPRESS

PRELIMINARY**CY7C1471V25****CY7C1473V25****CY7C1475V25**

72-Mbit (2M x 36/4M x 18/1M x 72) Flow-Through SRAM with NoBL™ Architecture

Features

- **No Bus Latency™ (NoBL™) architecture eliminates dead cycles between write and read cycles.**
- **Can support up to 133-MHz bus operations with zero wait states**
- **Data is transferred on every clock**
- **Pin compatible and functionally equivalent to ZBT™ devices**
- **Internally self-timed output buffer control to eliminate the need to use OE**
- **Registered inputs for flow-through operation**
- **Byte Write capability**
- **2.5V/1.8V I/O power supply**
- **Fast clock-to-output times**
 - 6.5 ns (for 133-MHz device)
 - 8.5 ns (for 100-MHz device)
- **Clock Enable (CEN) pin to enable clock and suspend operation**
- **Synchronous self-timed writes**
- **Asynchronous Output Enable**
- **Offered in JEDEC-standard lead-free 100 TQFP, and 165-ball fBGA packages for CY7C1471V25 and CY7C1473V25. 209-ball fBGA package for CY7C1475V25.**
- **Three chip enables for simple depth expansion.**
- **Automatic Power-down feature available using ZZ mode or CE deselect.**
- **JTAG boundary scan for BGA and fBGA packages**
- **Burst Capability—linear or interleaved burst order**
- **Low standby power**

Functional Description^[1]

The CY7C1471V25, CY7C1473V25 and CY7C1475V25 are 2.5V, 2M x 36/4M x 18/1M x 72 Synchronous Flow-through Burst SRAMs designed specifically to support unlimited true back-to-back Read/Write operations without the insertion of wait states. The CY7C1471V25, CY7C1473V25 and CY7C1475V25 are equipped with the advanced No Bus Latency (NoBL) logic required to enable consecutive Read/Write operations with data being transferred on every clock cycle. This feature dramatically improves the throughput of data through the SRAM, especially in systems that require frequent Write-Read transitions.

All synchronous inputs pass through input registers controlled by the rising edge of the clock. The clock input is qualified by the Clock Enable (CEN) signal, which when deasserted suspends operation and extends the previous clock cycle. Maximum access delay from the clock rise is 6.5 ns (133-MHz device).

Write operations are controlled by the two or four Byte Write Select (BW_X) and a Write Enable (WE) input. All writes are conducted with on-chip synchronous self-timed write circuitry.

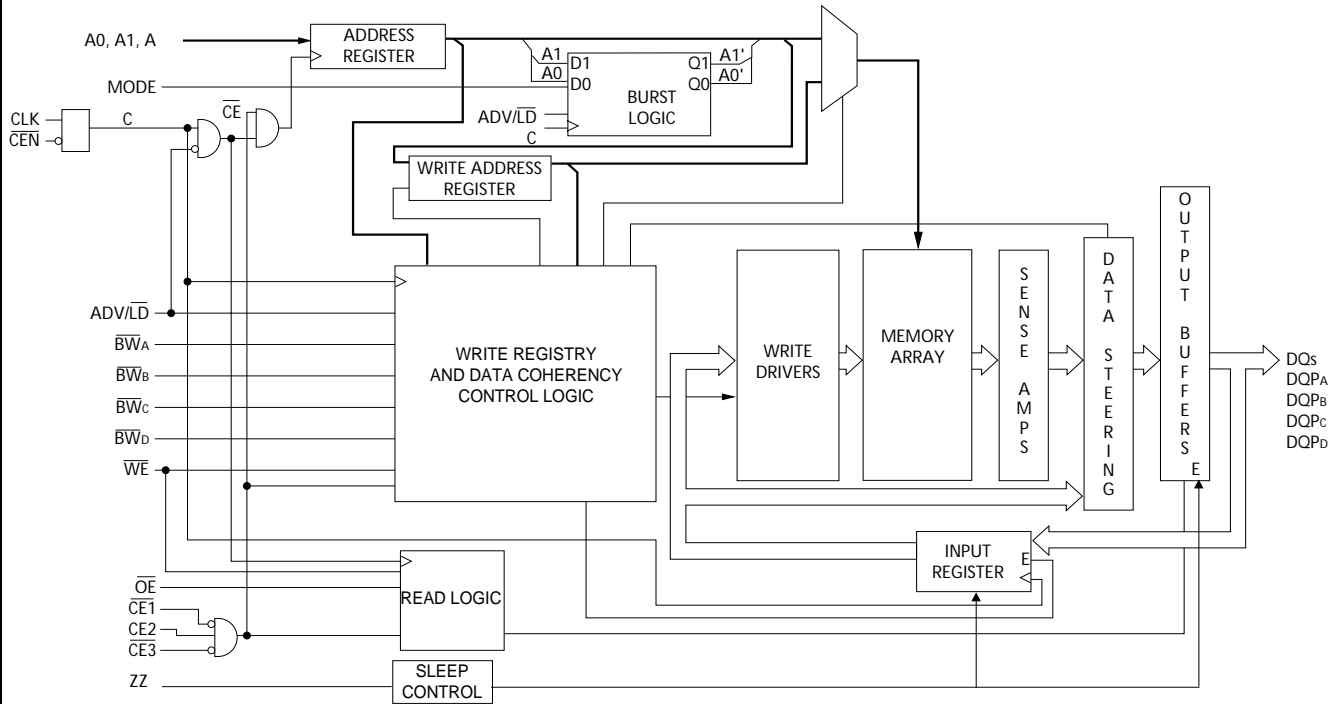
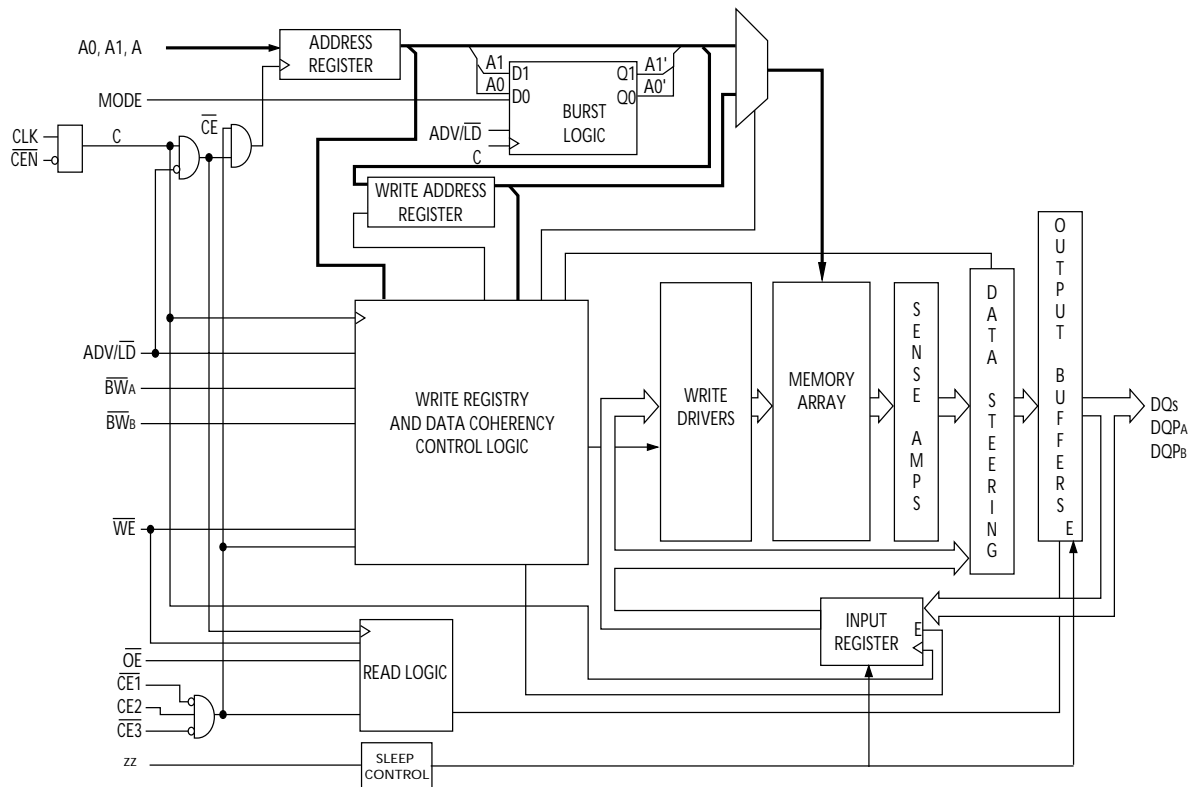
Three synchronous Chip Enables (\overline{CE}_1 , CE₂, \overline{CE}_3) and an asynchronous Output Enable (OE) provide for easy bank selection and output tri-state control. In order to avoid bus contention, the output drivers are synchronously tri-stated during the data portion of a write sequence.

Selection Guide

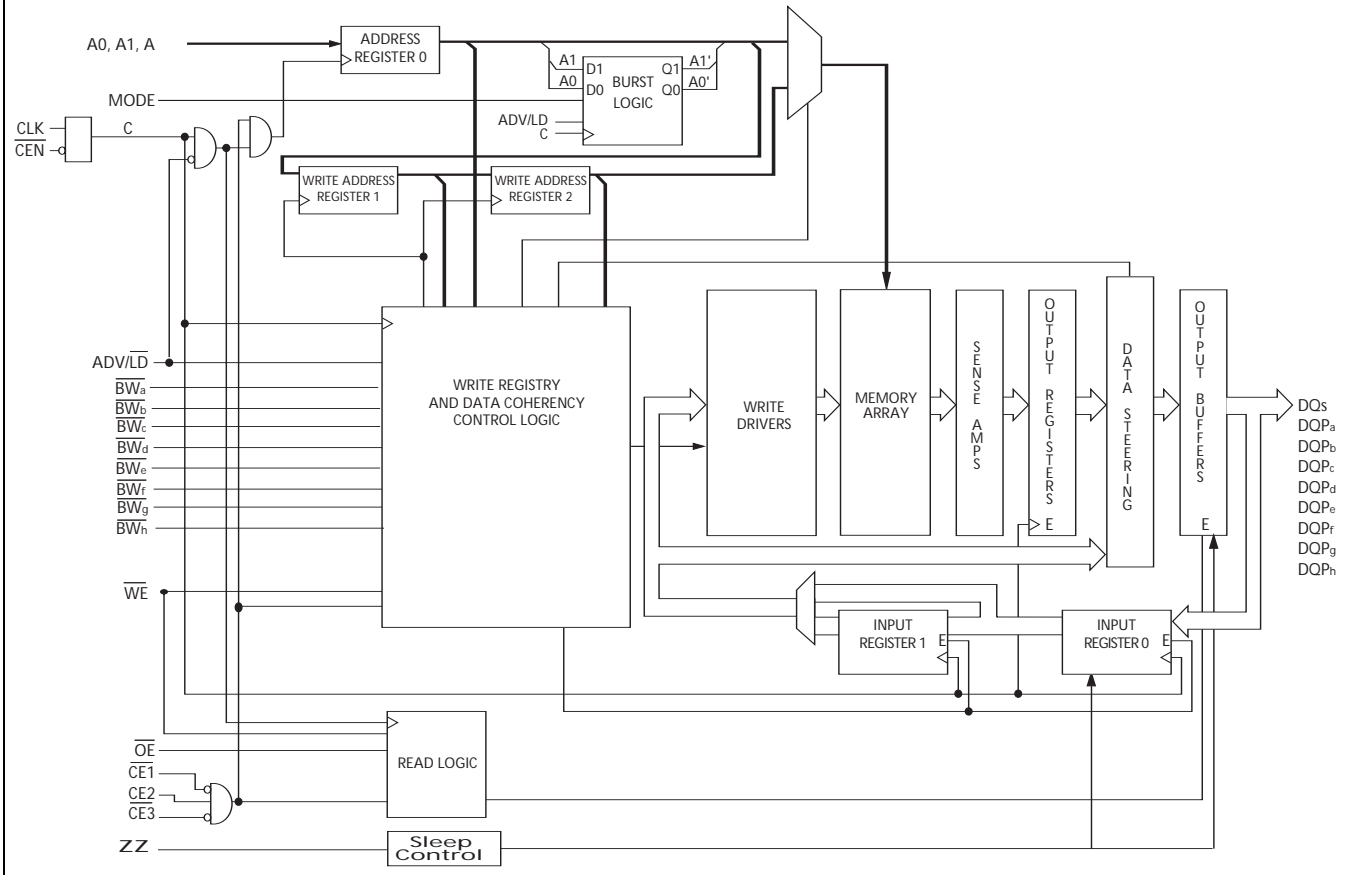
| | 133 MHz | 100 MHz | Unit |
|------------------------------|---------|---------|------|
| Maximum Access Time | 6.5 | 8.5 | ns |
| Maximum Operating Current | 305 | 275 | mA |
| Maximum CMOS Standby Current | 120 | 120 | mA |

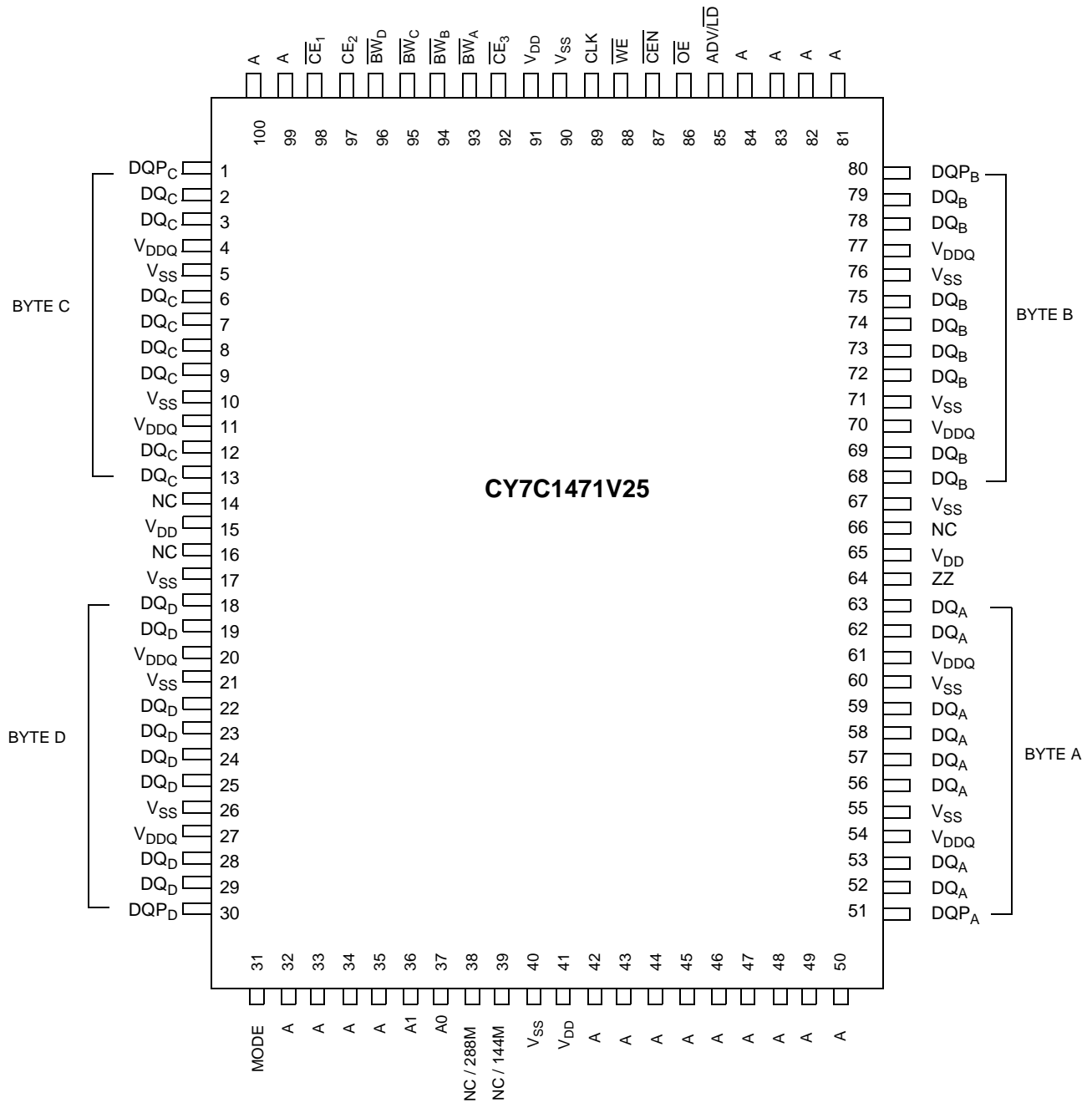
Note:

1. For best-practices recommendations, please refer to the Cypress application note *System Design Guidelines* on www.cypress.com.

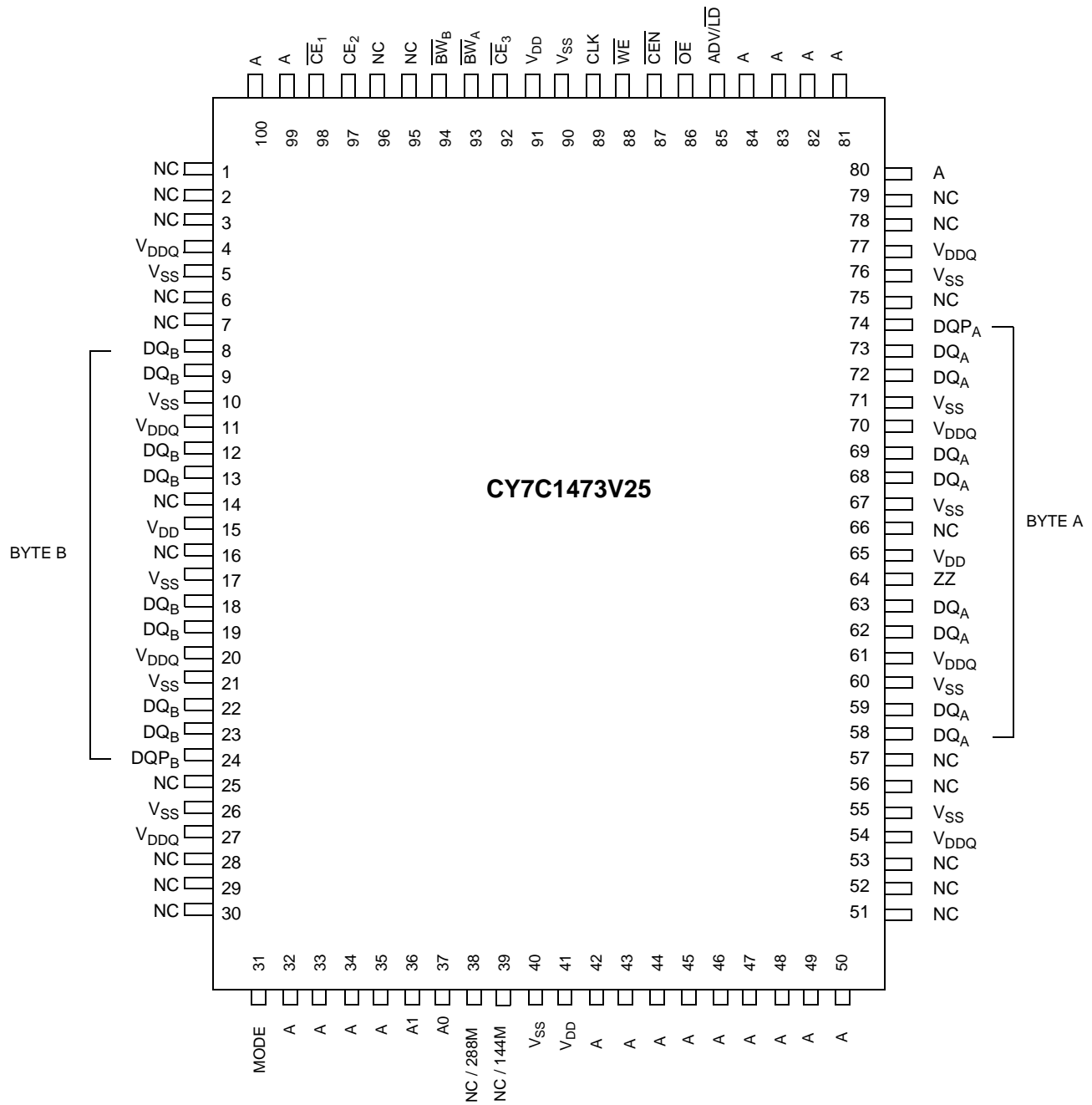
Logic Block Diagram – CY7C1471V25 (2M x 36)

Logic Block Diagram – CY7C1473V25 (4M x 18)


Logic Block Diagram – CY7C1475V25 (1M x 72)



Pin Configurations
100-lead TQFP


Pin Configurations (continued)

100-lead TQFP




PRELIMINARY

CY7C1471V25
CY7C1473V25
CY7C1475V25

Pin Configurations (continued)

165-ball fBGA (3 Chip Enable with JTAG)
CY7C1471V25 (2M x 36)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|----------|------------------|-----------------|-------------------|-------------------|-------------------|-------------------|------------------|-----------------|------------------|-----------------|------------------|
| A | NC / 288M | A | \overline{CE}_1 | \overline{BW}_C | \overline{BW}_B | \overline{CE}_3 | \overline{CEN} | ADV/LD | A | A | NC |
| B | NC | A | CE2 | \overline{BW}_D | \overline{BW}_A | CLK | \overline{WE} | \overline{OE} | A | A | NC / 144M |
| C | DQP _C | NC | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | NC | DQP _B |
| D | DQ _C | DQ _C | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _B | DQ _B |
| E | DQ _C | DQ _C | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _B | DQ _B |
| F | DQ _C | DQ _C | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _B | DQ _B |
| G | DQ _C | DQ _C | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _B | DQ _B |
| H | NC | NC | NC | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | NC | NC | ZZ |
| J | DQ _D | DQ _D | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _A | DQ _A |
| K | DQ _D | DQ _D | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _A | DQ _A |
| L | DQ _D | DQ _D | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _A | DQ _A |
| M | DQ _D | DQ _D | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _A | DQ _A |
| N | DQP _D | NC | V _{DDQ} | V _{SS} | NC | NC | NC | V _{SS} | V _{DDQ} | NC | DQP _A |
| P | NC | A | A | A | TDI | A1 | TDO | A | A | A | NC |
| R | MODE | A | A | A | TMS | A0 | TCK | A | A | A | A |

CY7C1473V25 (4M x 18)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|----------|------------------|-----------------|-------------------|-------------------|-------------------|-------------------|------------------|-----------------|------------------|-----------------|------------------|
| A | NC / 288M | A | \overline{CE}_1 | \overline{BW}_B | NC | \overline{CE}_3 | \overline{CEN} | ADV/LD | A | A | A |
| B | NC | A | CE2 | NC | \overline{BW}_A | CLK | \overline{WE} | \overline{OE} | A | A | NC / 144M |
| C | NC | NC | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | NC | DQP _A |
| D | NC | DQ _B | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | NC | DQ _A |
| E | NC | DQ _B | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | NC | DQ _A |
| F | NC | DQ _B | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | NC | DQ _A |
| G | NC | DQ _B | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | NC | DQ _A |
| H | NC | NC | NC | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | NC | NC | ZZ |
| J | DQ _B | NC | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _A | NC |
| K | DQ _B | NC | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _A | NC |
| L | DQ _B | NC | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _A | NC |
| M | DQ _B | NC | V _{DDQ} | V _{DD} | V _{SS} | V _{SS} | V _{SS} | V _{DD} | V _{DDQ} | DQ _A | NC |
| N | DQP _B | NC | V _{DDQ} | V _{SS} | NC | NC | NC | V _{SS} | V _{DDQ} | NC | NC |
| P | NC | A | A | A | TDI | A1 | TDO | A | A | A | NC |
| R | MODE | A | A | A | TMS | A0 | TCK | A | A | A | A |



PRELIMINARY

**CY7C1471V25
CY7C1473V25
CY7C1475V25**

Pin Configurations (continued)

209-ball PBGA

CY7C1475V25 (1M × 72)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|----------|------|------|------------------|------------------|-----------------|-----------------|-----------------|------------------|------------------|------|------|
| A | DQg | DQg | A | CE ₂ | A | ADV/LD | A | CE ₃ | A | DQb | DQb |
| B | DQg | DQg | BWS _c | BWS _g | NC | WE | A | BWS _b | BWS _f | DQb | DQb |
| C | DQg | DQg | BWS _h | BWS _d | NC | CE ₁ | NC | BWS _e | BWS _a | DQb | DQb |
| D | DQg | DQg | V _{SS} | NC | NC | OE | NC | NC | V _{SS} | DQb | DQb |
| E | DQPg | DQPc | V _{DDQ} | V _{DDQ} | V _{DD} | V _{DD} | V _{DD} | V _{DDQ} | V _{DDQ} | DQPf | DQPb |
| F | DQc | DQc | V _{SS} | V _{SS} | V _{SS} | NC | V _{SS} | V _{SS} | V _{SS} | DQf | DQf |
| G | DQc | DQc | V _{DDQ} | V _{DDQ} | V _{DD} | NC | V _{DD} | V _{DDQ} | V _{DDQ} | DQf | DQf |
| H | DQc | DQc | V _{SS} | V _{SS} | V _{SS} | NC | V _{SS} | V _{SS} | V _{SSQ} | DQf | DQf |
| J | DQc | DQc | V _{DDQ} | V _{DDQ} | V _{DD} | NC | V _{DD} | V _{DDQ} | V _{DDQ} | DQf | DQf |
| K | NC | NC | CLK | NC | V _{SS} | CEN | V _{SS} | NC | NC | NC | NC |
| L | DQh | DQh | V _{DDQ} | V _{DDQ} | V _{DD} | NC | V _{DD} | V _{DDQ} | V _{DDQ} | DQa | DQa |
| M | DQh | DQh | V _{SS} | V _{SS} | V _{SS} | NC | V _{SS} | V _{SS} | V _{SS} | DQa | DQa |
| N | DQh | DQh | V _{DDQ} | V _{DDQ} | V _{DD} | NC | V _{DD} | V _{DDQ} | V _{DDQ} | DQa | DQa |
| P | DQh | DQh | V _{SS} | V _{SS} | V _{SS} | ZZ | V _{SS} | V _{SS} | V _{SS} | DQa | DQa |
| R | DQPd | DQPh | V _{DDQ} | V _{DDQ} | V _{DD} | V _{DD} | V _{DD} | V _{DDQ} | V _{DDQ} | DQPa | DQPe |
| T | DQd | DQd | V _{SS} | NC | NC | MODE | NC | NC | V _{SS} | DQe | DQe |
| U | DQd | DQd | NC | A | A | A | A | A | NC | DQe | DQe |
| V | DQd | DQd | A | A | A | A1 | A | A | A | DQe | DQe |
| W | DQd | DQd | TMS | TDI | A | A0 | A | TDO | TCK | DQe | DQe |

Pin Definitions

| Name | I/O | Description |
|--|--------------------|--|
| A ₀ , A ₁ , A | Input-Synchronous | Address Inputs used to select one of the address locations. Sampled at the rising edge of the CLK. A _[1:0] are fed to the two-bit burst counter. |
| BW _A , BW _B , BW _C , BW _D , BW _E , BW _F , BW _G , BW _H | Input-Synchronous | Byte Write Inputs, active LOW. Qualified with \overline{WE} to conduct writes to the SRAM. Sampled on the rising edge of CLK. |
| \overline{WE} | Input-Synchronous | Write Enable Input, active LOW. Sampled on the rising edge of CLK if \overline{CEN} is active LOW. This signal must be asserted LOW to initiate a write sequence. |
| ADV/LD | Input-Synchronous | Advance/Load Input. Used to advance the on-chip address counter or load a new address. When HIGH (and \overline{CEN} is asserted LOW) the internal burst counter is advanced. When LOW, a new address can be loaded into the device for an access. After being deselected, ADV/LD should be driven LOW in order to load a new address. |
| CLK | Input-Clock | Clock Input. Used to capture all synchronous inputs to the device. CLK is qualified with \overline{CEN} . CLK is only recognized if \overline{CEN} is active LOW. |
| \overline{CE}_1 | Input-Synchronous | Chip Enable 1 Input, active LOW. Sampled on the rising edge of CLK. Used in conjunction with \overline{CE}_2 , and \overline{CE}_3 to select/deselect the device. |
| \overline{CE}_2 | Input-Synchronous | Chip Enable 2 Input, active HIGH. Sampled on the rising edge of CLK. Used in conjunction with \overline{CE}_1 and \overline{CE}_3 to select/deselect the device. |
| \overline{CE}_3 | Input-Synchronous | Chip Enable 3 Input, active LOW. Sampled on the rising edge of CLK. Used in conjunction with \overline{CE}_1 and \overline{CE}_2 to select/deselect the device. |
| \overline{OE} | Input-Asynchronous | Output Enable, asynchronous input, active LOW. Combined with the synchronous logic block inside the device to control the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are tri-stated, and act as input data pins. \overline{OE} is masked during the data portion of a write sequence, during the first clock when emerging from a deselected state, when the device has been deselected. |
| \overline{CEN} | Input-Synchronous | Clock Enable Input, active LOW. When asserted LOW the Clock signal is recognized by the SRAM. When deasserted HIGH the Clock signal is masked. Since deasserting \overline{CEN} does not deselect the device, \overline{CEN} can be used to extend the previous cycle when required. |
| ZZ | Input-Asynchronous | ZZ "Sleep" Input. This active HIGH input places the device in a non-time critical "sleep" condition with data integrity preserved. During normal operation, this pin can be connected to V _{SS} or left floating. |
| DQ _s | I/O-Synchronous | Bidirectional Data I/O lines. As inputs, they feed into an on-chip data register that is triggered by the rising edge of CLK. As outputs, they deliver the data contained in the memory location specified by the addresses presented during the previous clock rise of the read cycle. The direction of the pins is controlled by \overline{OE} . When \overline{OE} is asserted LOW, the pins behave as outputs. When HIGH, DQ _s and DQP _x are placed in a tri-state condition. The outputs are automatically tri-stated during the data portion of a write sequence, during the first clock when emerging from a deselected state, and when the device is deselected, regardless of the state of \overline{OE} . |
| DQP _x | I/O-Synchronous | Bidirectional Data Parity I/O Lines. Functionally, these signals are identical to DQ _s . During write sequences, DQP _x is controlled by BW _x correspondingly. |
| MODE | Input Strap Pin | Mode Input. Selects the burst order of the device. When tied to Gnd selects linear burst sequence. When tied to V _{DD} or left floating selects interleaved burst sequence. |
| V _{DD} | Power Supply | Power supply inputs to the core of the device. |
| V _{DDQ} | I/O Power Supply | Power supply for the I/O circuitry. |
| V _{SS} | Ground | Ground for the device. |

Pin Definitions (continued)

| Name | I/O | Description |
|------|-----------------------------------|---|
| TDO | JTAG serial output Synchronous | Serial data-out to the JTAG circuit. Delivers data on the negative edge of TCK. If the JTAG feature is not being utilized, this pin should be left unconnected. This pin is not available on TQFP packages. |
| TDI | JTAG serial input Synchronous | Serial data-In to the JTAG circuit. Sampled on the rising edge of TCK. If the JTAG feature is not being utilized, this pin can be left floating or connected to V_{DD} through a pull up resistor. This pin is not available on TQFP packages. |
| TMS | JTAG serial input Synchronous | Serial data-In to the JTAG circuit. Sampled on the rising edge of TCK. If the JTAG feature is not being utilized, this pin can be disconnected or connected to V_{DD} . This pin is not available on TQFP packages. |
| TCK | JTAG-Clock | Clock input to the JTAG circuitry. If the JTAG feature is not being utilized, this pin must be connected to V_{SS} . This pin is not available on TQFP packages. |
| NC | - | No Connects. Not internally connected to the die. 144M and 288M are address expansion pins and are not internally connected to the die. |

Functional Overview

The CY7C1471V25, CY7C1473V25 and CY7C1475V25 are synchronous flow-through burst SRAMs designed specifically to eliminate wait states during Write-Read transitions. All synchronous inputs pass through input registers controlled by the rising edge of the clock. The clock signal is qualified with the Clock Enable input signal (\overline{CEN}). If \overline{CEN} is HIGH, the clock signal is not recognized and all internal states are maintained. All synchronous operations are qualified with \overline{CEN} . Maximum access delay from the clock rise (t_{CDV}) is 6.5 ns (133-MHz device).

Accesses can be initiated by asserting all three Chip Enables (\overline{CE}_1 , \overline{CE}_2 , \overline{CE}_3) active at the rising edge of the clock. If Clock Enable (\overline{CEN}) is active LOW and $\overline{ADV/LD}$ is asserted LOW, the address presented to the device will be latched. The access can either be a Read or Write operation, depending on the status of the Write Enable (\overline{WE}). BW_X can be used to conduct Byte Write operations.

Write operations are qualified by the Write Enable (\overline{WE}). All writes are simplified with on-chip synchronous self-timed write circuitry.

Three synchronous Chip Enables (\overline{CE}_1 , \overline{CE}_2 , \overline{CE}_3) and an asynchronous Output Enable (\overline{OE}) simplify depth expansion. All operations (Reads, Writes, and Deselects) are pipelined. $\overline{ADV/LD}$ should be driven LOW once the device has been deselected in order to load a new address for the next operation.

Single Read Accesses

A Read access is initiated when the following conditions are satisfied at clock rise: (1) \overline{CEN} is asserted LOW, (2) \overline{CE}_1 , \overline{CE}_2 , and \overline{CE}_3 are ALL asserted active, (3) the Write Enable input signal \overline{WE} is deasserted HIGH, and 4) $\overline{ADV/LD}$ is asserted LOW. The address presented to the address inputs is latched into the Address Register and presented to the memory array and control logic. The control logic determines that a read access is in progress and allows the requested data to propagate to the output buffers. The data is available within 6.5 ns (133-MHz device) provided \overline{OE} is active LOW. After the first clock of the read access, the output buffers are controlled by \overline{OE} and the internal control logic. \overline{OE} must be driven LOW in order for the device to drive out the requested data. On the subsequent clock, another operation (Read/Write/Deselect)

can be initiated. When the SRAM is deselected at clock rise by one of the chip enable signals, its output will be tri-stated immediately.

Burst Read Accesses

The CY7C1471V25, CY7C1473V25 and CY7C1475V25 has an on-chip burst counter that allows the user the ability to supply a single address and conduct up to four Reads without reasserting the address inputs. $\overline{ADV/LD}$ must be driven LOW in order to load a new address into the SRAM, as described in the Single Read Access section above. The sequence of the burst counter is determined by the MODE input signal. A LOW input on MODE selects a linear burst mode, a HIGH selects an interleaved burst sequence. Both burst counters use A0 and A1 in the burst sequence, and will wrap around when incremented sufficiently. A HIGH input on $\overline{ADV/LD}$ will increment the internal burst counter regardless of the state of chip enable inputs or \overline{WE} . \overline{WE} is latched at the beginning of a burst cycle. Therefore, the type of access (Read or Write) is maintained throughout the burst sequence.

Single Write Accesses

Write accesses are initiated when the following conditions are satisfied at clock rise: (1) \overline{CEN} is asserted LOW, (2) \overline{CE}_1 , \overline{CE}_2 , and \overline{CE}_3 are ALL asserted active, and (3) the write signal \overline{WE} is asserted LOW. The address presented to the address bus is loaded into the Address Register. The write signals are latched into the Control Logic block. The data lines are automatically tri-stated regardless of the state of the \overline{OE} input signal. This allows the external logic to present the data on DQs and DQP_X.

On the next clock rise the data presented to DQs and DQP_X (or a subset for Byte Write operations, see truth table for details) inputs is latched into the device and the write is complete. Additional accesses (Read/Write/Deselect) can be initiated on this cycle.

The data written during the Write operation is controlled by BW_X signals. The CY7C1471V25, CY7C1473V25 and CY7C1475V25 provide Byte Write capability that is described in the truth table. Asserting the Write Enable input (\overline{WE}) with the selected Byte Write Select input will selectively write to only the desired bytes. Bytes not selected during a Byte Write operation will remain unaltered. A synchronous self-timed Write mechanism has been provided to simplify the Write

operations. Byte Write capability has been included in order to greatly simplify Read/Modify/Write sequences, which can be reduced to simple byte write operations.

Because the CY7C1471V25, CY7C1473V25 and CY7C1475V25 are common I/O devices, data should not be driven into the device while the outputs are active. The Output Enable (OE) can be deasserted HIGH before presenting data to the DQs and DQP_X inputs. Doing so will tri-state the output drivers. As a safety precaution, DQs and DQP_X are automatically tri-stated during the data portion of a Write cycle, regardless of the state of OE.

Burst Write Accesses

The CY7C1471V25, CY7C1473V25 and CY7C1475V25 have an on-chip burst counter that allows the user the ability to supply a single address and conduct up to four Write operations without reasserting the address inputs. ADV/LD must be driven LOW in order to load the initial address, as described in the Single Write Access section above. When ADV/LD is driven HIGH on the subsequent clock rise, the Chip Enables (CE₁, CE₂, and CE₃) and WE inputs are ignored and the burst counter is incremented. The correct BW_X inputs must be driven in each cycle of the Burst Write, in order to write the correct bytes of data.

Sleep Mode

The ZZ input pin is an asynchronous input. Asserting ZZ places the SRAM in a power conservation "sleep" mode. Two clock cycles are required to enter into or exit from this "sleep" mode. While in this mode, data integrity is guaranteed. Accesses pending when entering the "sleep" mode are not considered valid nor is the completion of the operation guaranteed. The device must be deselected prior to entering the "sleep" mode. CE₁, CE₂, and CE₃, must remain inactive for the duration of t_{ZZREC} after the ZZ input returns LOW.

ZZ Mode Electrical Characteristics

| Parameter | Description | Test Conditions | Min. | Max. | Unit |
|--------------------|-----------------------------------|-----------------------------|-------------------|-------------------|------|
| I _{DDZZ} | Sleep mode standby current | ZZ ≥ V _{DD} – 0.2V | | 120 | mA |
| t _{ZZS} | Device operation to ZZ | ZZ ≥ V _{DD} – 0.2V | | 2t _{CYC} | ns |
| t _{ZZREC} | ZZ recovery time | ZZ ≤ 0.2V | 2t _{CYC} | | ns |
| t _{ZZI} | ZZ active to sleep current | This parameter is sampled | | 2t _{CYC} | ns |
| t _{RZZI} | ZZ Inactive to exit sleep current | This parameter is sampled | 0 | | ns |

Interleaved Burst Address Table (MODE = Floating or V_{DD})

| First Address A1: A0 | Second Address A1: A0 | Third Address A1: A0 | Fourth Address A1: A0 |
|-------------------------|--------------------------|-------------------------|--------------------------|
| 00 | 01 | 10 | 11 |
| 01 | 00 | 11 | 10 |
| 10 | 11 | 00 | 01 |
| 11 | 10 | 01 | 00 |

Linear Burst Address Table (MODE = GND)

| First Address A1: A0 | Second Address A1: A0 | Third Address A1: A0 | Fourth Address A1: A0 |
|-------------------------|--------------------------|-------------------------|--------------------------|
| 00 | 01 | 10 | 11 |
| 01 | 10 | 11 | 00 |
| 10 | 11 | 00 | 01 |
| 11 | 00 | 01 | 10 |

Truth Table^[2, 3, 4, 5, 6, 7, 8]

| Operation | Address Used | \overline{CE}_1 | CE_2 | \overline{CE}_3 | ZZ | ADV/LD | \overline{WE} | \overline{BW}_X | \overline{OE} | \overline{CEN} | CLK | DQ |
|-------------------------------|--------------|-------------------|--------|-------------------|----|--------|-----------------|-------------------|-----------------|------------------|------|--------------|
| Deselect Cycle | None | H | X | X | L | L | X | X | X | L | L->H | Tri-State |
| Deselect Cycle | None | X | X | H | L | L | X | X | X | L | L->H | Tri-State |
| Deselect Cycle | None | X | L | X | L | L | X | X | X | L | L->H | Tri-State |
| Continue Deselect Cycle | None | X | X | X | L | H | X | X | X | L | L->H | Tri-State |
| Read Cycle (Begin Burst) | External | L | H | L | L | L | H | X | L | L | L->H | Data Out (Q) |
| Read Cycle (Continue Burst) | Next | X | X | X | L | H | X | X | L | L | L->H | Data Out (Q) |
| NOP/Dummy Read (Begin Burst) | External | L | H | L | L | L | H | X | H | L | L->H | Tri-State |
| Dummy Read (Continue Burst) | Next | X | X | X | L | H | X | X | H | L | L->H | Tri-State |
| Write Cycle (Begin Burst) | External | L | H | L | L | L | L | L | X | L | L->H | Data In (D) |
| Write Cycle (Continue Burst) | Next | X | X | X | L | H | X | L | X | L | L->H | Data In (D) |
| NOP/Write Abort (Begin Burst) | None | L | H | L | L | L | L | H | X | L | L->H | Tri-State |
| Write Abort (Continue Burst) | Next | X | X | X | L | H | X | H | X | L | L->H | Tri-State |
| Ignore Clock Edge (Stall) | Current | X | X | X | L | X | X | X | X | H | L->H | - |
| Sleep Mode | None | X | X | X | H | X | X | X | X | X | X | Tri-State |

Truth Table for Read/Write^[2, 3, 9]

| Function (CY7C1471V25) | \overline{WE} | \overline{BW}_A | \overline{BW}_B | \overline{BW}_C | \overline{BW}_D |
|--|-----------------|-------------------|-------------------|-------------------|-------------------|
| Read | H | X | X | X | X |
| Write No bytes written | L | H | H | H | H |
| Write Byte A – (DQ _A and DQP _A) | L | L | H | H | H |
| Write Byte B – (DQ _B and DQP _B) | L | H | L | H | H |
| Write Byte C – (DQ _C and DQP _C) | L | H | H | L | H |
| Write Byte D – (DQ _D and DQP _D) | L | H | H | H | L |
| Write All Bytes | L | L | L | L | L |

Notes:

- X = "Don't Care." H = Logic HIGH, L = Logic LOW. \overline{BW}_X = L signifies at least one Byte Write Select is active, \overline{BW}_X = Valid signifies that the desired Byte Write Selects are asserted, see Truth Table for details.
- Write is defined by \overline{BW}_X , and \overline{WE} . See Truth Table for Read/Write.
- When a Write cycle is detected, all I/Os are tri-stated, even during Byte Writes.
- The DQs and DQP_X pins are controlled by the current cycle and the \overline{OE} signal. \overline{OE} is asynchronous and is not sampled with the clock.
- \overline{CEN} = H, inserts wait states.
- Device will power-up deselected and the I/Os in a tri-state condition, regardless of \overline{OE} .
- \overline{OE} is asynchronous and is not sampled with the clock rise. It is masked internally during write cycles. During a read cycle DQs and DQP_X = Tri-state when \overline{OE} is inactive or when the device is deselected, and DQs and DQP_X = data when \overline{OE} is active.
- Table only lists a partial listing of the byte write combinations. Any Combination of \overline{BW}_X is valid. Appropriate write will be done based on which byte write is active.

Truth Table for Read/Write^[2, 3, 9]

| Function (CY7C1473V25) | \overline{WE} | \overline{BW}_b | \overline{BW}_a |
|--|-----------------|-------------------|-------------------|
| Read | H | X | X |
| Write – No Bytes Written | L | H | H |
| Write Byte a – (DQ _a and DQP _a) | L | H | L |
| Write Byte b – (DQ _b and DQP _b) | L | L | H |
| Write Both Bytes | L | L | L |

Truth Table for Read/Write^[2, 3, 9]

| Function (CY7C1475V25) | \overline{WE} | \overline{BW}_x |
|--|-----------------|-------------------------|
| Read | H | X |
| Write – No Bytes Written | L | H |
| Write Byte X – (DQ _x and DQP _x) | L | L |
| Write All Bytes | L | All $\overline{BW} = L$ |

IEEE 1149.1 Serial Boundary Scan (JTAG)

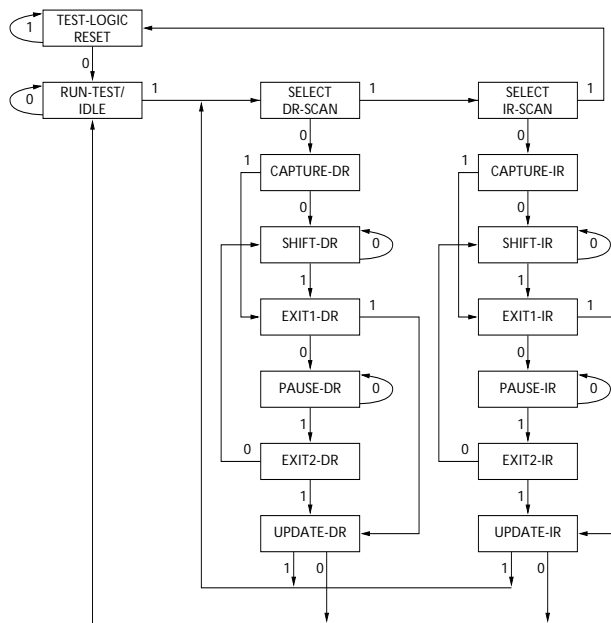
The CY7C1471V25, CY7C1473V25, and CY7C1475V25 and incorporate a serial boundary scan test access port (TAP). This port operates in accordance with IEEE Standard 1149.1-1990 but does not have the set of functions required for full 1149.1 compliance. These functions from the IEEE specification are excluded because their inclusion places an added delay in the critical speed path of the SRAM. Note that the TAP controller functions in a manner that does not conflict with the operation of other devices using 1149.1 fully compliant TAPs. The TAP operates using JEDEC-standard 2.5V or 1.8V I/O logic levels.

The CY7C1471V25, CY7C1473V25, and CY7C1475V25 contain a TAP controller, instruction register, boundary scan register, bypass register, and ID register.

Disabling the JTAG Feature

It is possible to operate the SRAM without using the JTAG feature. To disable the TAP controller, TCK must be tied LOW (V_{SS}) to prevent clocking of the device. TDI and TMS are internally pulled up and may be unconnected. They may alternately be connected to V_{DD} through a pull-up resistor. TDO should be left unconnected. Upon power-up, the device will come up in a reset state which will not interfere with the operation of the device.

TAP Controller State Diagram



The 0/1 next to each state represents the value of TMS at the rising edge of TCK.

Test Access Port (TAP)

Test Clock (TCK)

The test clock is used only with the TAP controller. All inputs are captured on the rising edge of TCK. All outputs are driven from the falling edge of TCK.

Test MODE SELECT (TMS)

The TMS input is used to give commands to the TAP controller and is sampled on the rising edge of TCK. It is allowable to leave this ball unconnected if the TAP is not used. The ball is pulled up internally, resulting in a logic HIGH level.

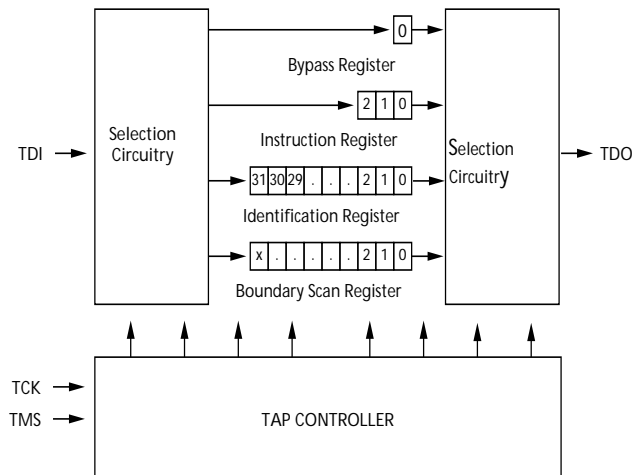
Test Data-In (TDI)

The TDI ball is used to serially input information into the registers and can be connected to the input of any of the registers. The register between TDI and TDO is chosen by the instruction that is loaded into the instruction register. For information on loading the instruction register, see the TAP Controller State Diagram. TDI is internally pulled up and can be unconnected if the TAP is unused in an application. TDI is connected to the most significant bit (MSB) of any register. (See Tap Controller Block Diagram.)

Test Data-Out (TDO)

The TDO output ball is used to serially clock data-out from the registers. The output is active depending upon the current state of the TAP state machine. The output changes on the falling edge of TCK. TDO is connected to the least significant bit (LSB) of any register. (See Tap Controller State Diagram.)

TAP Controller Block Diagram



Performing a TAP Reset

A RESET is performed by forcing TMS HIGH (V_{DD}) for five rising edges of TCK. This RESET does not affect the operation of the SRAM and may be performed while the SRAM is operating.

At power-up, the TAP is reset internally to ensure that TDO comes up in a High-Z state.

TAP Registers

Registers are connected between the TDI and TDO balls and allow data to be scanned into and out of the SRAM test circuitry. Only one register can be selected at a time through the instruction register. Data is serially loaded into the TDI ball on the rising edge of TCK. Data is output on the TDO ball on the falling edge of TCK.

Instruction Register

Three-bit instructions can be serially loaded into the instruction register. This register is loaded when it is placed between the TDI and TDO balls as shown in the Tap Controller Block Diagram. Upon power-up, the instruction register is loaded with the IDCODE instruction. It is also loaded with the IDCODE instruction if the controller is placed in a reset state as described in the previous section.

When the TAP controller is in the Capture-IR state, the two least significant bits are loaded with a binary "01" pattern to allow for fault isolation of the board-level serial test data path.

Bypass Register

To save time when serially shifting data through registers, it is sometimes advantageous to skip certain chips. The bypass register is a single-bit register that can be placed between the TDI and TDO balls. This allows data to be shifted through the SRAM with minimal delay. The bypass register is set LOW (V_{SS}) when the BYPASS instruction is executed.

Boundary Scan Register

The boundary scan register is connected to all the input and bidirectional balls on the SRAM.

The boundary scan register is loaded with the contents of the RAM I/O ring when the TAP controller is in the Capture-DR state and is then placed between the TDI and TDO balls when the controller is moved to the Shift-DR state. The EXTEST, SAMPLE/PRELOAD and SAMPLE Z instructions can be used to capture the contents of the I/O ring.

The Boundary Scan Order tables show the order in which the bits are connected. Each bit corresponds to one of the bumps on the SRAM package. The MSB of the register is connected to TDI and the LSB is connected to TDO.

Identification (ID) Register

The ID register is loaded with a vendor-specific, 32-bit code during the Capture-DR state when the IDCODE command is loaded in the instruction register. The IDCODE is hardwired into the SRAM and can be shifted out when the TAP controller is in the Shift-DR state. The ID register has a vendor code and other information described in the Identification Register Definitions table.

TAP Instruction Set

Overview

Eight different instructions are possible with the three-bit instruction register. All combinations are listed in the Instruction Codes table. Three of these instructions are listed as RESERVED and should not be used. The other five instructions are described in detail below.

The TAP controller used in this SRAM is not fully compliant to the 1149.1 convention because some of the mandatory 1149.1 instructions are not fully implemented.

The TAP controller cannot be used to load address data or control signals into the SRAM and cannot preload the I/O buffers. The SRAM does not implement the 1149.1 commands EXTEST or INTEST or the PRELOAD portion of SAMPLE/PRELOAD; rather, it performs a capture of the I/O ring when these instructions are executed.

Instructions are loaded into the TAP controller during the Shift-IR state when the instruction register is placed between TDI and TDO. During this state, instructions are shifted through the instruction register through the TDI and TDO balls. To execute the instruction once it is shifted in, the TAP controller needs to be moved into the Update-IR state.

EXTEST

EXTEST is a mandatory 1149.1 instruction which is to be executed whenever the instruction register is loaded with all 0s. EXTEST is not implemented in this SRAM TAP controller, and therefore this device is not compliant to 1149.1. The TAP controller does recognize an all-0 instruction.

When an EXTEST instruction is loaded into the instruction register, the SRAM responds as if a SAMPLE/PRELOAD instruction has been loaded. There is one difference between the two instructions. Unlike the SAMPLE/PRELOAD instruction, EXTEST places the SRAM outputs in a High-Z state.

IDCODE

The IDCODE instruction causes a vendor-specific, 32-bit code to be loaded into the instruction register. It also places the instruction register between the TDI and TDO balls and allows the IDCODE to be shifted out of the device when the TAP controller enters the Shift-DR state.

The IDCODE instruction is loaded into the instruction register upon power-up or whenever the TAP controller is given a test logic reset state.

SAMPLE Z

The SAMPLE Z instruction causes the boundary scan register to be connected between the TDI and TDO balls when the TAP controller is in a Shift-DR state. It also places all SRAM outputs into a High-Z state.

SAMPLE/PRELOAD

SAMPLE/PRELOAD is a 1149.1 mandatory instruction. The PRELOAD portion of this instruction is not implemented, so the device TAP controller is not fully 1149.1 compliant.

When the SAMPLE/PRELOAD instruction is loaded into the instruction register and the TAP controller is in the Capture-DR state, a snapshot of data on the inputs and bidirectional balls is captured in the boundary scan register.

The user must be aware that the TAP controller clock can only operate at a frequency up to 20 MHz, while the SRAM clock operates more than an order of magnitude faster. Because there is a large difference in the clock frequencies, it is possible that during the Capture-DR state, an input or output will undergo a transition. The TAP may then try to capture a signal while in transition (metastable state). This will not harm the device, but there is no guarantee as to the value that will be captured. Repeatable results may not be possible.

To guarantee that the boundary scan register will capture the correct value of a signal, the SRAM signal must be stabilized long enough to meet the TAP controller's capture set-up plus hold time (t_{CS} plus t_{CH}).

The SRAM clock input might not be captured correctly if there is no way in a design to stop (or slow) the clock during a SAMPLE/PRELOAD instruction. If this is an issue, it is still

possible to capture all other signals and simply ignore the value of the CLK captured in the boundary scan register.

Once the data is captured, it is possible to shift out the data by putting the TAP into the Shift-DR state. This places the boundary scan register between the TDI and TDO balls.

Note that since the PRELOAD part of the command is not implemented, putting the TAP to the Update-DR state while performing a SAMPLE/PRELOAD instruction will have the same effect as the Pause-DR command.

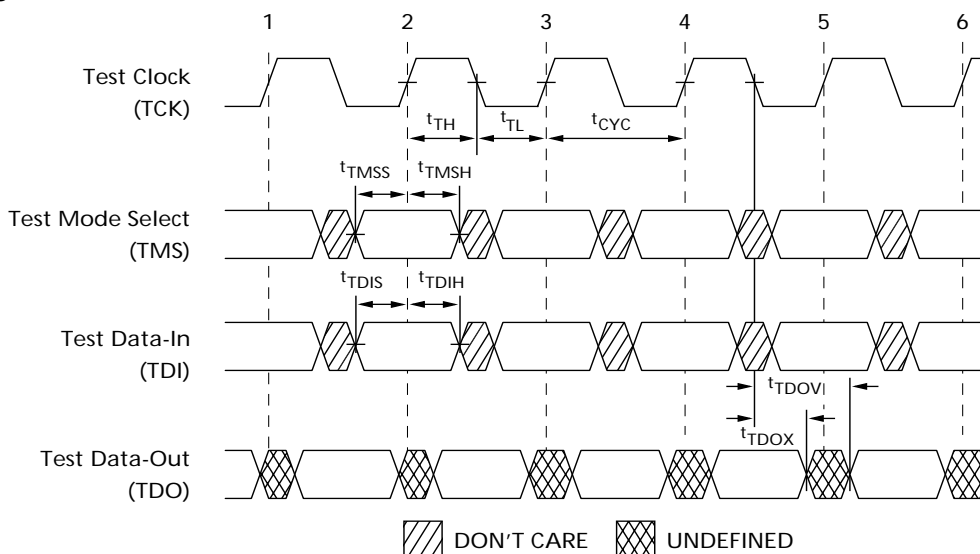
BYPASS

When the BYPASS instruction is loaded in the instruction register and the TAP is placed in a Shift-DR state, the bypass register is placed between the TDI and TDO balls. The advantage of the BYPASS instruction is that it shortens the boundary scan path when multiple devices are connected together on a board.

Reserved

These instructions are not implemented but are reserved for future use. Do not use these instructions.

TAP Timing



TAP AC Switching Characteristics Over the Operating Range^[10, 11]

| Parameter | Description | Min. | Max. | Unit |
|---------------------|-------------------------------|------|------|------|
| Clock | | | | |
| t_{TCYC} | TCK Clock Cycle Time | 50 | | ns |
| t_{TF} | TCK Clock Frequency | | 20 | MHz |
| t_{TH} | TCK Clock HIGH time | 25 | | ns |
| t_{TL} | TCK Clock LOW time | 25 | | ns |
| Output Times | | | | |
| t_{TDOV} | TCK Clock LOW to TDO Valid | | 5 | ns |
| t_{TDOX} | TCK Clock LOW to TDO Invalid | 0 | | ns |
| Set-up Times | | | | |
| t_{TMSS} | TMS Set-up to TCK Clock Rise | 5 | | ns |
| t_{TDis} | TDI Set-up to TCK Clock Rise | 5 | | ns |
| t_{CS} | Capture Set-up to TCK Rise | 5 | | ns |
| Hold Times | | | | |
| t_{TMSH} | TMS Hold after TCK Clock Rise | 5 | | ns |
| t_{TDIH} | TDI Hold after Clock Rise | 5 | | ns |
| t_{CH} | Capture Hold after Clock Rise | 5 | | ns |

Notes:

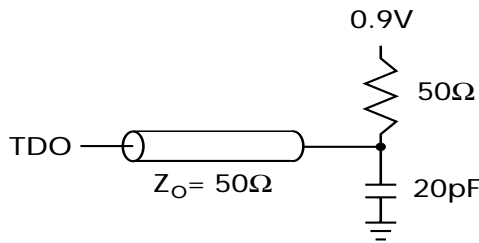
10. t_{CS} and t_{CH} refer to the set-up and hold time requirements of latching data from the boundary scan register.

11. Test conditions are specified using the load in TAP AC Test Conditions. $t_R/t_F = 1$ ns.

1.8V TAP AC Test Conditions

Input pulse levels 0.2V to $V_{DDQ} - 0.2$
 Input rise and fall time 1 ns
 Input timing reference levels 0.9V
 Output reference levels 0.9V
 Test load termination supply voltage 0.9V

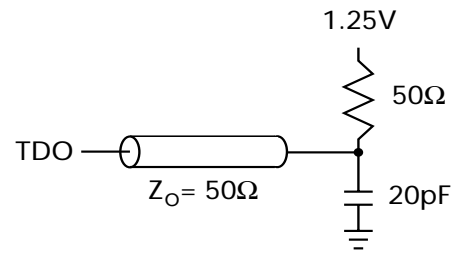
1.8V TAP AC Output Load Equivalent



2.5V TAP AC Test Conditions

Input pulse levels V_{SS} to 2.5V
 Input rise and fall time 1 ns
 Input timing reference levels 1.25V
 Output reference levels 1.25V
 Test load termination supply voltage 1.25V

2.5V TAP AC Output Load Equivalent



TAP DC Electrical Characteristics And Operating Conditions

(0°C < T_A < +70°C; V_{DD} = 2.375 to 2.625 unless otherwise noted)^[12]

| Parameter | Description | Test Conditions | Min. | Max. | Unit |
|------------------|---------------------|--|------|-----------------------|------|
| V _{OH1} | Output HIGH Voltage | I _{OH} = -1.0 mA, V _{DDQ} = 2.5V | 2.0 | | V |
| V _{OH2} | Output HIGH Voltage | I _{OH} = -100 μA, V _{DDQ} = 2.5V | 2.1 | | V |
| | | V _{DDQ} = 1.8V | 1.6 | | V |
| V _{OL1} | Output LOW Voltage | I _{OL} = 1.0 mA, V _{DDQ} = 2.5V | | 0.4 | V |
| V _{OL2} | Output LOW Voltage | I _{OL} = 100 μA, V _{DDQ} = 2.5V | | 0.2 | V |
| | | V _{DDQ} = 1.8V | | 0.2 | V |
| V _{IH} | Input HIGH Voltage | V _{DDQ} = 2.5V | 1.7 | V _{DD} + 0.3 | V |
| | | V _{DDQ} = 1.8V | 1.26 | V _{DD} + 0.3 | V |
| V _{IL} | Input LOW Voltage | V _{DDQ} = 2.5V | -0.3 | 0.7 | V |
| | | V _{DDQ} = 1.8V | -0.3 | 0.36 | V |
| I _X | Input Load Current | GND ≤ V _{IN} ≤ V _{DDQ} | -5 | 5 | μA |

Identification Register Definitions

| Instruction Field | CY7C1471V25 (2MX36) | CY7C1473V25 (4MX18) | CY7C1475V25 (1MX72) | Description |
|------------------------------------|------------------------|------------------------|------------------------|---|
| Revision Number (31:29) | 000 | 000 | 000 | Describes the version number |
| Device Depth (28:24) | 01011 | 01011 | 01011 | Reserved for internal use |
| Architecture/Memory Type(23:18) | 001001 | 001001 | 001001 | Defines memory type and architecture |
| Bus Width/Density(17:12) | 100100 | 010100 | 110100 | Defines width and density |
| Cypress JEDEC ID Code (11:1) | 00000110100 | 00000110100 | 00000110100 | Allows unique identification of SRAM vendor |
| ID Register Presence Indicator (0) | 1 | 1 | 1 | Indicates the presence of an ID register |

Note:

12. All voltages referenced to V_{SS} (GND).

Scan Register Sizes

| Register Name | Bit Size (x36) | Bit Size (x18) | Bit Size (x72) |
|-----------------------------|----------------|----------------|----------------|
| Instruction | 3 | 3 | 3 |
| Bypass | 1 | 1 | 1 |
| ID | 32 | 32 | 32 |
| Boundary Scan Order-165FBGA | 71 | 52 | - |
| Boundary Scan Order- 209BGA | - | - | 110 |

Identification Codes

| Instruction | Code | Description |
|----------------|------|---|
| EXTEST | 000 | Captures I/O ring contents. Places the boundary scan register between TDI and TDO. Forces all SRAM outputs to High-Z state. This instruction is not 1149.1 compliant. |
| IDCODE | 001 | Loads the ID register with the vendor ID code and places the register between TDI and TDO. This operation does not affect SRAM operations. |
| SAMPLE Z | 010 | Captures I/O ring contents. Places the boundary scan register between TDI and TDO. Forces all SRAM output drivers to a High-Z state. |
| RESERVED | 011 | Do Not Use: This instruction is reserved for future use. |
| SAMPLE/PRELOAD | 100 | Captures I/O ring contents. Places the boundary scan register between TDI and TDO. Does not affect SRAM operation. This instruction does not implement 1149.1 preload function and is therefore not 1149.1 compliant. |
| RESERVED | 101 | Do Not Use: This instruction is reserved for future use. |
| RESERVED | 110 | Do Not Use: This instruction is reserved for future use. |
| BYPASS | 111 | Places the bypass register between TDI and TDO. This operation does not affect SRAM operation. |



PRELIMINARY

**CY7C1471V25
CY7C1473V25
CY7C1475V25**

Boundary Scan Exit Order (x36)

| Bit # | 165-Ball ID |
|-------|-------------|
| 1 | C1 |
| 2 | D1 |
| 3 | E1 |
| 4 | D2 |
| 5 | E2 |
| 6 | F1 |
| 7 | G1 |
| 8 | F2 |
| 9 | G2 |
| 10 | J1 |
| 11 | K1 |
| 12 | L1 |
| 13 | J2 |
| 14 | M1 |
| 15 | N1 |
| 16 | K2 |
| 17 | L2 |
| 18 | M2 |
| 19 | R1 |
| 20 | R2 |
| 21 | R3 |
| 22 | P2 |
| 23 | R4 |
| 24 | P6 |
| 25 | R6 |
| 26 | N6 |
| 27 | P11 |
| 28 | R8 |
| 29 | P3 |
| 30 | P4 |
| 31 | P8 |
| 32 | P9 |
| 33 | P10 |
| 34 | R9 |
| 35 | R10 |
| 36 | R11 |
| 37 | N11 |

Boundary Scan Exit Order (x36) (continued)

| Bit # | 165-Ball ID |
|-------|-------------|
| 38 | M11 |
| 39 | L11 |
| 40 | M10 |
| 41 | L10 |
| 42 | K11 |
| 43 | J11 |
| 44 | K10 |
| 45 | J10 |
| 46 | H11 |
| 47 | G11 |
| 48 | F11 |
| 49 | E11 |
| 50 | D10 |
| 51 | D11 |
| 52 | C11 |
| 53 | G10 |
| 54 | F10 |
| 55 | E10 |
| 56 | A10 |
| 57 | B10 |
| 58 | A9 |
| 59 | B9 |
| 60 | A8 |
| 61 | B8 |
| 62 | A7 |
| 63 | B7 |
| 64 | B6 |
| 65 | A6 |
| 66 | B5 |
| 67 | A5 |
| 68 | A4 |
| 69 | B4 |
| 70 | B3 |
| 71 | A3 |
| 72 | A2 |
| 73 | B2 |



PRELIMINARY

**CY7C1471V25
CY7C1473V25
CY7C1475V25**

Boundary Scan Exit Order (x18)

| Bit # | 165-Ball ID |
|-------|-------------|
| 1 | D2 |
| 2 | E2 |
| 3 | F2 |
| 4 | G2 |
| 5 | J1 |
| 6 | K1 |
| 7 | L1 |
| 8 | M1 |
| 9 | N1 |
| 10 | R1 |
| 11 | R2 |
| 12 | R3 |
| 13 | P2 |
| 14 | R4 |
| 15 | P6 |
| 16 | R6 |
| 17 | N6 |
| 18 | P11 |
| 19 | R8 |
| 20 | P3 |
| 21 | P4 |
| 22 | P8 |
| 23 | P9 |
| 24 | P10 |
| 25 | R9 |
| 26 | R10 |
| 27 | R11 |
| 28 | M10 |
| 29 | L10 |
| 30 | K10 |
| 31 | J10 |
| 32 | H11 |
| 33 | G11 |
| 34 | F11 |
| 35 | E11 |
| 36 | D11 |
| 37 | C11 |
| 38 | A11 |
| 39 | A10 |
| 40 | B10 |
| 41 | A9 |
| 42 | B9 |
| 43 | A8 |
| 44 | B8 |

Boundary Scan Exit Order (x18) (continued)

| Bit # | 165-Ball ID |
|-------|-------------|
| 45 | A7 |
| 46 | B7 |
| 47 | B6 |
| 48 | A6 |
| 49 | B5 |
| 50 | A4 |
| 51 | B3 |
| 52 | A3 |
| 53 | A2 |
| 54 | B2 |

Boundary Scan Exit Order (x72)

| Bit # | 209-Ball ID |
|-------|-------------|
| 1 | A1 |
| 2 | A2 |
| 3 | B1 |
| 4 | B2 |
| 5 | C1 |
| 6 | C2 |
| 7 | D1 |
| 8 | D2 |
| 9 | E1 |
| 10 | E2 |
| 11 | F1 |
| 12 | F2 |
| 13 | G1 |
| 14 | G2 |
| 15 | H1 |
| 16 | H2 |
| 17 | J1 |
| 18 | J2 |
| 19 | L1 |
| 20 | L2 |
| 21 | M1 |
| 22 | M2 |
| 23 | N1 |
| 24 | N2 |
| 25 | P1 |
| 26 | P2 |
| 27 | R2 |
| 28 | R1 |
| 29 | T1 |
| 30 | T2 |



PRELIMINARY

**CY7C1471V25
CY7C1473V25
CY7C1475V25**

Boundary Scan Exit Order (x72) (continued)

| Bit # | 209-Ball ID |
|-------|-------------|
| 31 | U1 |
| 32 | U2 |
| 33 | V1 |
| 34 | V2 |
| 35 | W1 |
| 36 | W2 |
| 37 | T6 |
| 38 | V3 |
| 39 | V4 |
| 40 | U4 |
| 41 | W5 |
| 42 | V6 |
| 43 | W6 |
| 44 | U3 |
| 45 | U9 |
| 46 | V5 |
| 47 | U5 |
| 48 | U6 |
| 49 | W7 |
| 50 | V7 |
| 51 | U7 |
| 52 | V8 |
| 53 | V9 |
| 54 | W11 |
| 55 | W10 |
| 56 | V11 |
| 57 | V10 |
| 58 | U11 |
| 59 | U10 |
| 60 | T11 |
| 61 | T10 |
| 62 | R11 |
| 63 | R10 |
| 64 | P11 |
| 65 | P10 |
| 66 | N11 |
| 67 | N10 |
| 68 | M11 |
| 69 | M10 |
| 70 | L11 |
| 71 | L10 |
| 72 | P6 |
| 73 | J11 |
| 74 | J10 |

Boundary Scan Exit Order (x72) (continued)

| Bit # | 209-Ball ID |
|-------|-------------|
| 75 | H11 |
| 76 | H10 |
| 77 | G11 |
| 78 | G10 |
| 79 | F11 |
| 80 | F10 |
| 81 | E10 |
| 82 | E11 |
| 83 | D11 |
| 84 | D10 |
| 85 | C11 |
| 86 | C10 |
| 87 | B11 |
| 88 | B10 |
| 89 | A11 |
| 90 | A10 |
| 91 | A9 |
| 92 | U8 |
| 93 | A7 |
| 94 | A5 |
| 95 | A6 |
| 96 | D6 |
| 97 | B6 |
| 98 | D7 |
| 99 | K3 |
| 100 | A8 |
| 101 | B4 |
| 102 | B3 |
| 103 | C3 |
| 104 | C4 |
| 105 | C8 |
| 106 | C9 |
| 107 | B9 |
| 108 | B8 |
| 109 | A4 |
| 110 | C6 |
| 111 | B7 |
| 112 | A3 |



PRELIMINARY

CY7C1471V25
CY7C1473V25
CY7C1475V25

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with

Power Applied -55°C to +125°C

Supply Voltage on V_{DD} Relative to GND -0.5V to +3.6V

DC Voltage Applied to Outputs

in Tri-State -0.5V to $V_{DDQ} + 0.5V$

DC Input Voltage -0.5V to $V_{DD} + 0.5V$

Current into Outputs (LOW) 20 mA

Static Discharge Voltage >2001V
(per MIL-STD-883, Method 3015)

Latch-up Current >200 mA

Operating Range

| Range | Ambient Temperature | V_{DD} | V_{DDQ} |
|------------|---------------------|-------------|------------------|
| Commercial | 0°C to +70°C | 2.5V–5%/+5% | 1.7V to V_{DD} |

Electrical Characteristics Over the Operating Range^[13, 14]

| Parameter | Description | Test Conditions | Min. | Max. | Unit |
|-----------|---|--|-----------------------|-----------------|---------|
| V_{DD} | Power Supply Voltage | | 2.375 | 2.625 | V |
| V_{DDQ} | I/O Supply Voltage | $V_{DDQ} = 2.5V$ | 2.375 | V_{DD} | V |
| | | $V_{DDQ} = 1.8V$ | 1.7 | 1.9 | V |
| V_{OH} | Output HIGH Voltage | $V_{DD} = \text{Min.}, I_{OH} = -1.0 \text{ mA}, V_{DDQ} = 2.5V$ | 2.0 | | V |
| | | $V_{DD} = \text{Min.}, I_{OH} = -100 \mu A, V_{DDQ} = 1.8V$ | 1.6 | | V |
| V_{OL} | Output LOW Voltage | $V_{DD} = \text{Min.}, I_{OL} = 1.0 \text{ mA}, V_{DDQ} = 2.5V$ | | 0.4 | V |
| | | $V_{DD} = \text{Min.}, I_{OL} = 100 \mu A, V_{DDQ} = 1.8V$ | | 0.2 | V |
| V_{IH} | Input HIGH Voltage ^[13] | $V_{DDQ} = 2.5V$ | 1.7 | $V_{DD} + 0.3V$ | V |
| | | $V_{DDQ} = 1.8V$ | 1.26 | $V_{DD} + 0.3V$ | V |
| V_{IL} | Input LOW Voltage ^[13] | $V_{DDQ} = 2.5V$ | -0.3 | 0.7 | V |
| | | $V_{DDQ} = 1.8V$ | -0.3 | 0.36 | V |
| I_X | Input Load Current except ZZ and MODE | $GND \leq V_I \leq V_{DDQ}$ | -5 | 5 | μA |
| | Input Current of MODE | Input = V_{SS} | -5 | | μA |
| | | Input = V_{DD} | | 30 | μA |
| | Input Current of ZZ | Input = V_{SS} | -30 | | μA |
| | | Input = V_{DD} | | 5 | μA |
| I_{OZ} | Output Leakage Current | $GND \leq V_I \leq V_{DDQ}$, Output Disabled | -5 | 5 | μA |
| I_{DD} | V_{DD} Operating Supply Current | $V_{DD} = \text{Max.}, I_{OUT} = 0 \text{ mA}, f = f_{MAX} = 1/t_{CYC}$ | 6.5-ns cycle, 133 MHz | 305 | mA |
| | | | 8.5-ns cycle, 100 MHz | 275 | mA |
| I_{SB1} | Automatic CE Power-down Current—TTL Inputs | $V_{DD} = \text{Max.}$, Device Deselected, $V_{IN} \geq V_{IH}$ or $V_{IN} \leq V_{IL}$, $f = f_{MAX}$, inputs switching | 6.5-ns cycle, 133 MHz | 170 | mA |
| | | | 8.5-ns cycle, 100 MHz | 170 | mA |
| I_{SB2} | Automatic CE Power-down Current—CMOS Inputs | $V_{DD} = \text{Max.}$, Device Deselected, $V_{IN} \leq 0.3V$ or $V_{IN} \geq V_{DD} - 0.3V$, $f = 0$, inputs static | All speeds | 120 | mA |
| I_{SB3} | Automatic CE Power-down Current—CMOS Inputs | $V_{DD} = \text{Max.}$, Device Deselected, or $V_{IN} \leq 0.3V$ or $V_{IN} \geq V_{DDQ} - 0.3V$, $f = f_{MAX}$, inputs switching | 6.5-ns cycle, 133 MHz | 170 | mA |
| | | | 8.5-ns cycle, 100 MHz | 170 | mA |
| I_{SB4} | Automatic CE Power-down Current—TTL Inputs | $V_{DD} = \text{Max.}$, Device Deselected, $V_{IN} \geq V_{DD} - 0.3V$ or $V_{IN} \leq 0.3V$, $f = 0$, inputs static | All Speeds | 135 | mA |

Notes:

13. Overshoot: $V_{IH}(AC) < V_{DD} + 1.5V$ (Pulse width less than $t_{CYC}/2$), undershoot: $V_{IL}(AC) > -2V$ (Pulse width less than $t_{CYC}/2$).

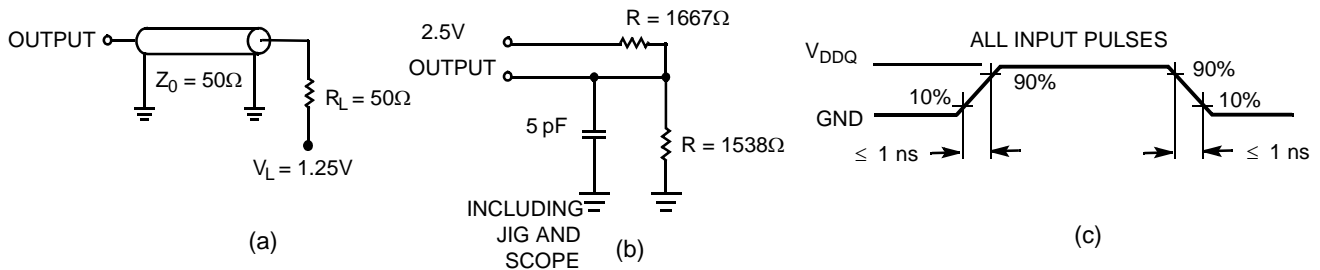
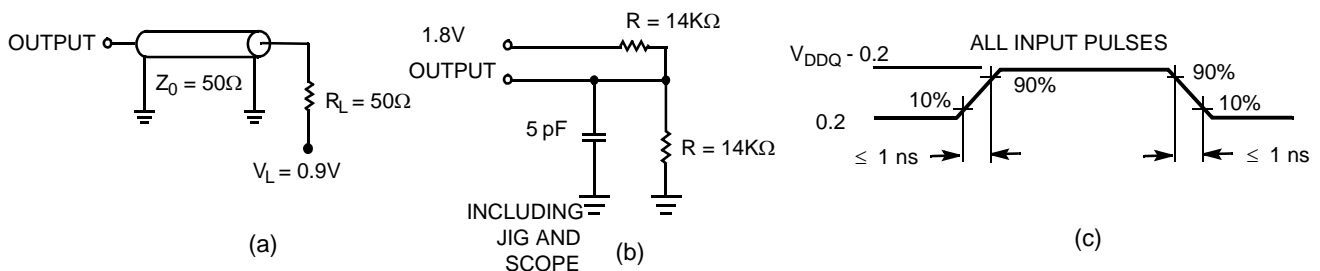
14. $T_{Power-up}$: Assumes a linear ramp from 0V to $V_{DD}(\text{min.})$ within 200 ms. During this time $V_{IH} \leq V_{DD}$ and $V_{DDQ} \leq V_{DD}$.

Thermal Resistance^[15]

| Parameter | Description | Test Conditions | 165 fBGA Package | 209 BGA Package | TQFP Package | Unit |
|---------------|--|--|------------------|-----------------|--------------|------|
| Θ_{JA} | Thermal Resistance (Junction to Ambient) | Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA / JESD51. | 16.3 | 15.2 | 24.63 | °C/W |
| Θ_{JC} | Thermal Resistance (Junction to Case) | | 2.1 | 1.7 | 2.28 | °C/W |

Capacitance^[15]

| Parameter | Description | Test Conditions | TQFP Max. | 209-BGA Max. | 165-fBGA Max. | Unit |
|---------------|---------------------------|--|-----------|--------------|---------------|------|
| $C_{ADDRESS}$ | Address Input Capacitance | $T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$, $V_{DD} = 2.5\text{V}$, $V_{DDQ} = 2.5\text{V}$ | 6 | 6 | 6 | pF |
| C_{DATA} | Data Input Capacitance | | 5 | 5 | 5 | pF |
| C_{CTRL} | Control Input Capacitance | | 8 | 8 | 8 | pF |
| C_{CLK} | Clock Input Capacitance | | 6 | 6 | 6 | pF |
| $C_{I/O}$ | Input/Output Capacitance | | 5 | 5 | 5 | pF |

AC Test Loads and Waveforms
2.5V I/O Test Load

1.8V I/O Test Load

Note:

15. Tested initially and after any design or process change that may affect these parameters



PRELIMINARY

**CY7C1471V25
CY7C1473V25
CY7C1475V25**

Switching Characteristics Over the Operating Range^[20, 21]

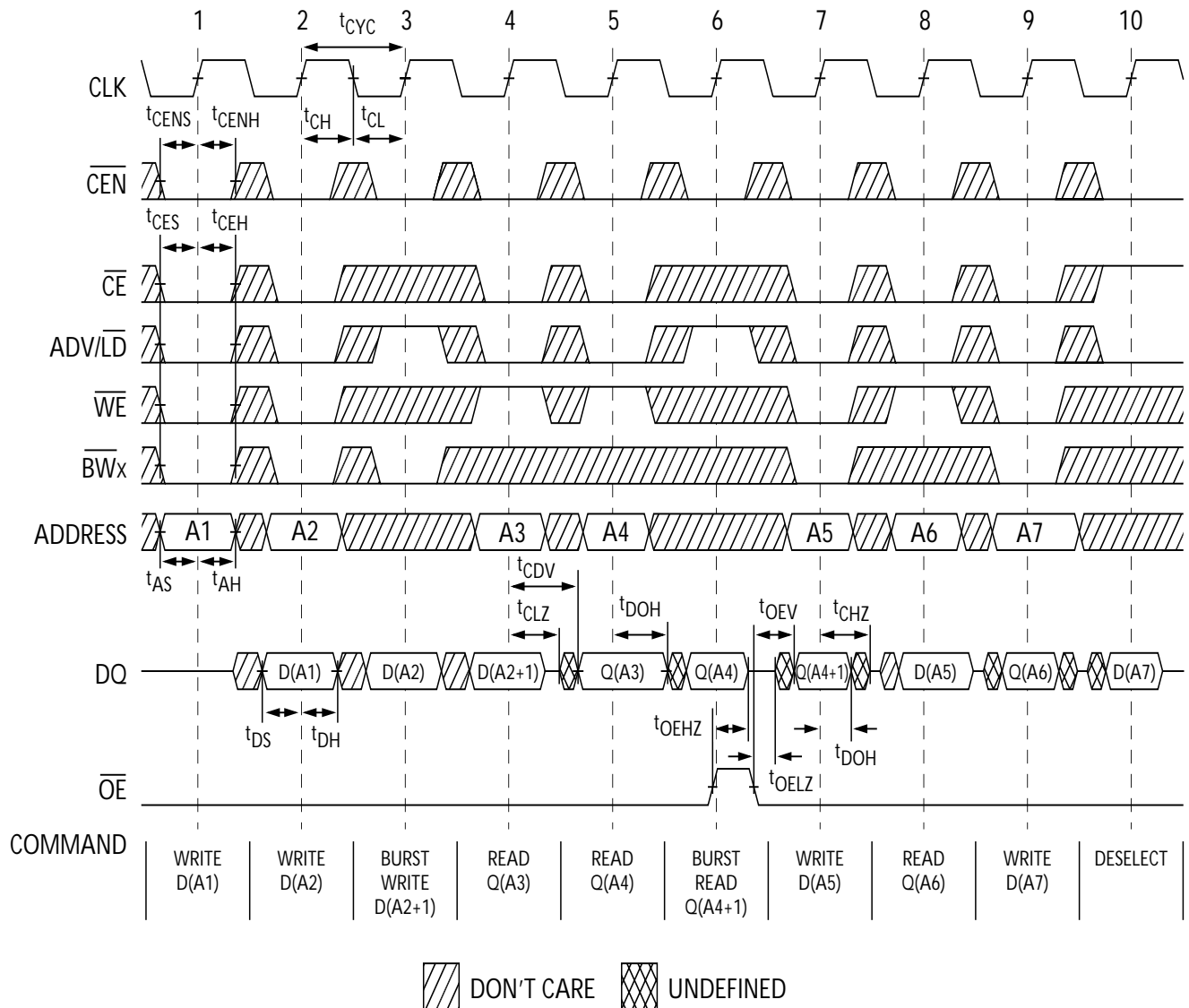
| Parameter | Description | 133 MHz | | 100 MHz | | Unit |
|---------------------------------|---|---------|------|---------|------|------|
| | | Min. | Max. | Min. | Max. | |
| t _{POWER} [*] | | 1 | | 1 | | ms |
| Clock | | | | | | |
| t _{CYC} | Clock Cycle Time | 7.5 | | 10 | | ns |
| t _{CH} | Clock HIGH | 2.5 | | 3.0 | | ns |
| t _{CL} | Clock LOW | 2.5 | | 3.0 | | ns |
| Output Times | | | | | | |
| t _{CDV} | Data Output Valid After CLK Rise | | 6.5 | | 8.5 | ns |
| t _{DOH} | Data Output Hold After CLK Rise | 2.5 | | 2.5 | | ns |
| t _{CLZ} | Clock to Low-Z ^[17, 18, 19] | 3.0 | | 3.0 | | ns |
| t _{CHZ} | Clock to High-Z ^[17, 18, 19] | | 3.8 | | 4.5 | ns |
| t _{OEV} | $\overline{\text{OE}}$ LOW to Output Valid | | 3.0 | | 3.8 | ns |
| t _{OELZ} | $\overline{\text{OE}}$ LOW to Output Low-Z ^[17, 18, 19] | 0 | | 0 | | ns |
| t _{OEHZ} | $\overline{\text{OE}}$ HIGH to Output High-Z ^[17, 18, 19] | | 3.0 | | 4.0 | ns |
| Set-up Times | | | | | | |
| t _{AS} | Address Set-up Before CLK Rise | 1.5 | | 1.5 | | ns |
| t _{ALS} | ADV/LD Set-up Before CLK Rise | 1.5 | | 1.5 | | ns |
| t _{WES} | $\overline{\text{WE}}$, $\overline{\text{BW}}_{\text{X}}$ Set-up Before CLK Rise | 1.5 | | 1.5 | | ns |
| t _{CENS} | $\overline{\text{CEN}}$ Set-up Before CLK Rise | 1.5 | | 1.5 | | ns |
| t _{DS} | Data Input Set-up Before CLK Rise | 1.5 | | 1.5 | | ns |
| t _{CES} | Chip Enable Set-Up Before CLK Rise | 1.5 | | 1.5 | | ns |
| Hold Times | | | | | | |
| t _{AH} | Address Hold After CLK Rise | 0.5 | | 0.5 | | ns |
| t _{ALH} | ADV/LD Hold After CLK Rise | 0.5 | | 0.5 | | ns |
| t _{WEH} | $\overline{\text{WE}}$, $\overline{\text{BW}}_{\text{X}}$ Hold After CLK Rise | 0.5 | | 0.5 | | ns |
| t _{CENH} | $\overline{\text{CEN}}$ Hold After CLK Rise | 0.5 | | 0.5 | | ns |
| t _{DH} | Data Input Hold After CLK Rise | 0.5 | | 0.5 | | ns |
| t _{CEH} | Chip Enable Hold After CLK Rise | 0.5 | | 0.5 | | ns |

Notes:

16. This part has a voltage regulator internally; t_{POWER} is the time that the power needs to be supplied above V_{DD}(minimum) initially, before a read or write operation can be initiated.
17. t_{CHZ}, t_{CLZ}, t_{OELZ}, and t_{OEHZ} are specified with AC test conditions shown in part (b) of AC Test Loads. Transition is measured ± 200 mV from steady-state voltage.
18. At any given voltage and temperature, t_{OEHZ} is less than t_{OELZ} and t_{CHZ} is less than t_{CLZ} to eliminate bus contention between SRAMs when sharing the same data bus. These specifications do not imply a bus contention condition, but reflect parameters guaranteed over worst case user conditions. Device is designed to achieve High-Z prior to Low-Z under the same system conditions.
19. This parameter is sampled and not 100% tested.
20. Timing reference level is 1.25V when V_{DDQ} = 2.5V and is 0.9V when V_{DDQ} = 1.8V.
21. Test conditions shown in (a) of AC Test Loads unless otherwise noted.

Switching Waveforms

Read/Write Waveforms^[22, 23, 24]

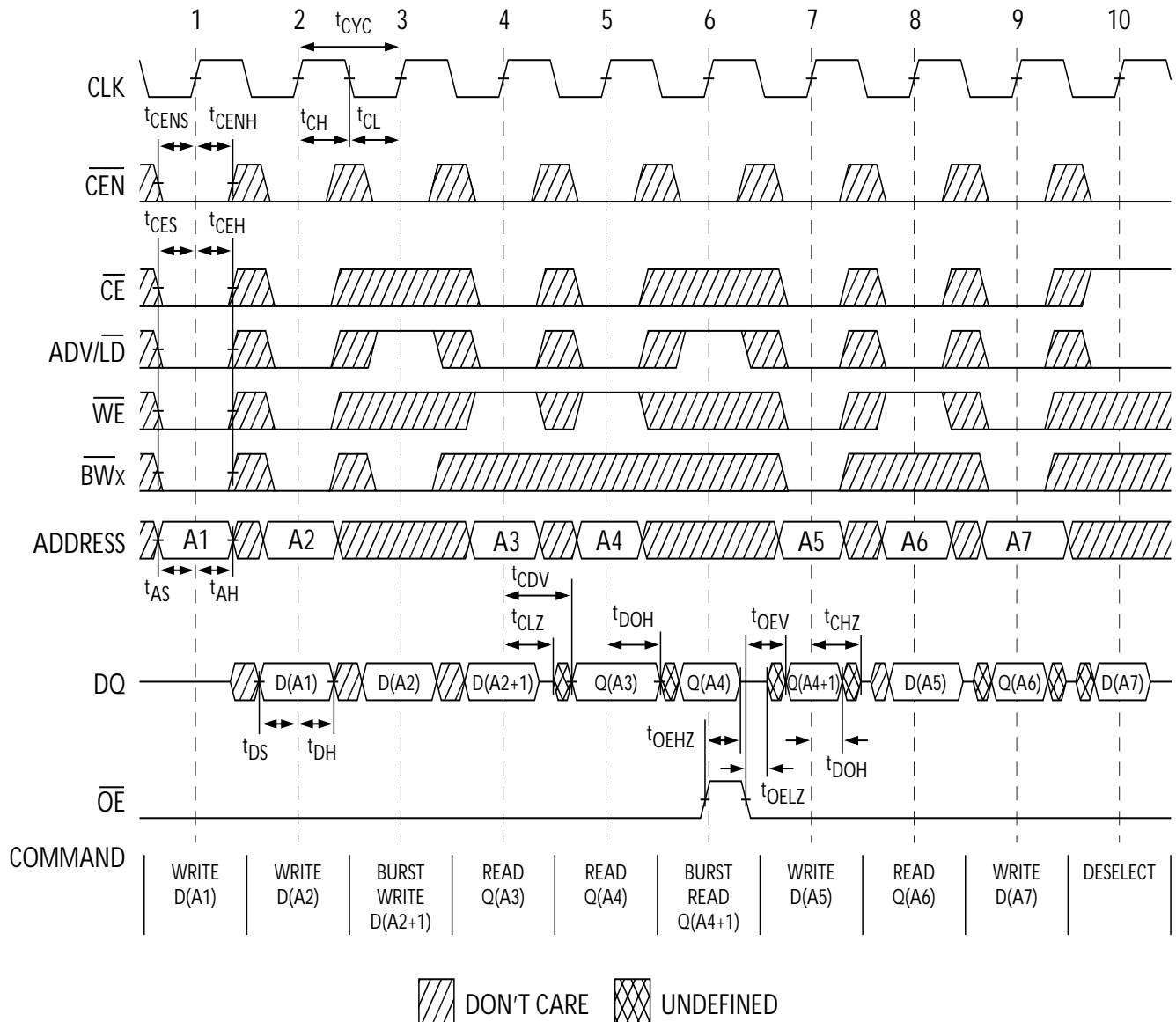


Notes:

22. For this waveform ZZ is tied LOW.

23. When \overline{CE} is LOW, \overline{CE}_1 is LOW, CE_2 is HIGH and \overline{CE}_3 is LOW. When \overline{CE} is HIGH, \overline{CE}_1 is HIGH or CE_2 is LOW or \overline{CE}_3 is HIGH.

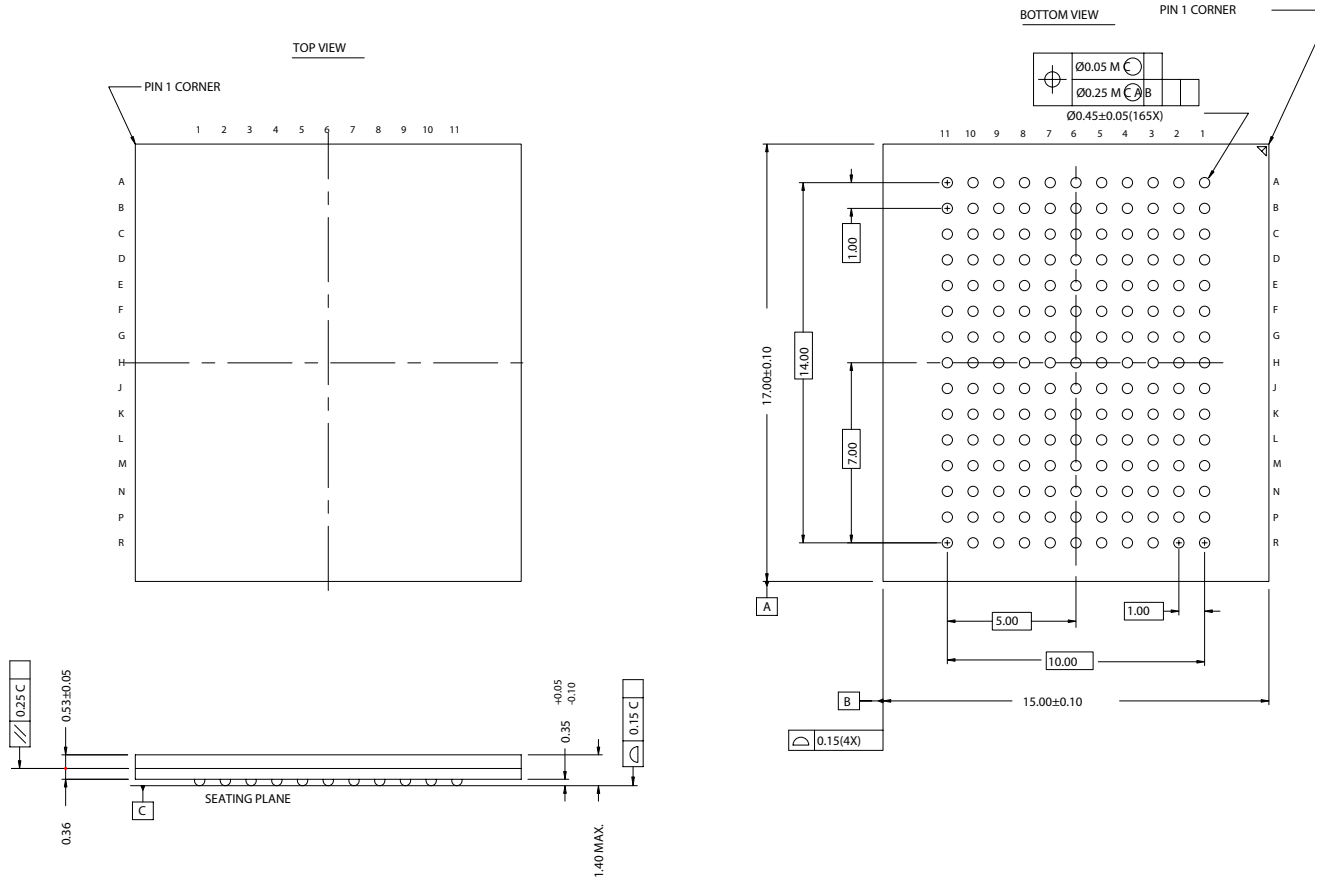
24. Order of the Burst sequence is determined by the status of the MODE (0 = Linear, 1 = Interleaved). Burst operations are optional.

Switching Waveforms (continued)
NOP, STALL and DESELECT Cycles^[22, 23, 25]

Note:

25. The IGNORE CLOCK EDGE or STALL cycle (Clock 3) illustrates \overline{CEN} being used to create a pause. A write is not performed during this cycle.

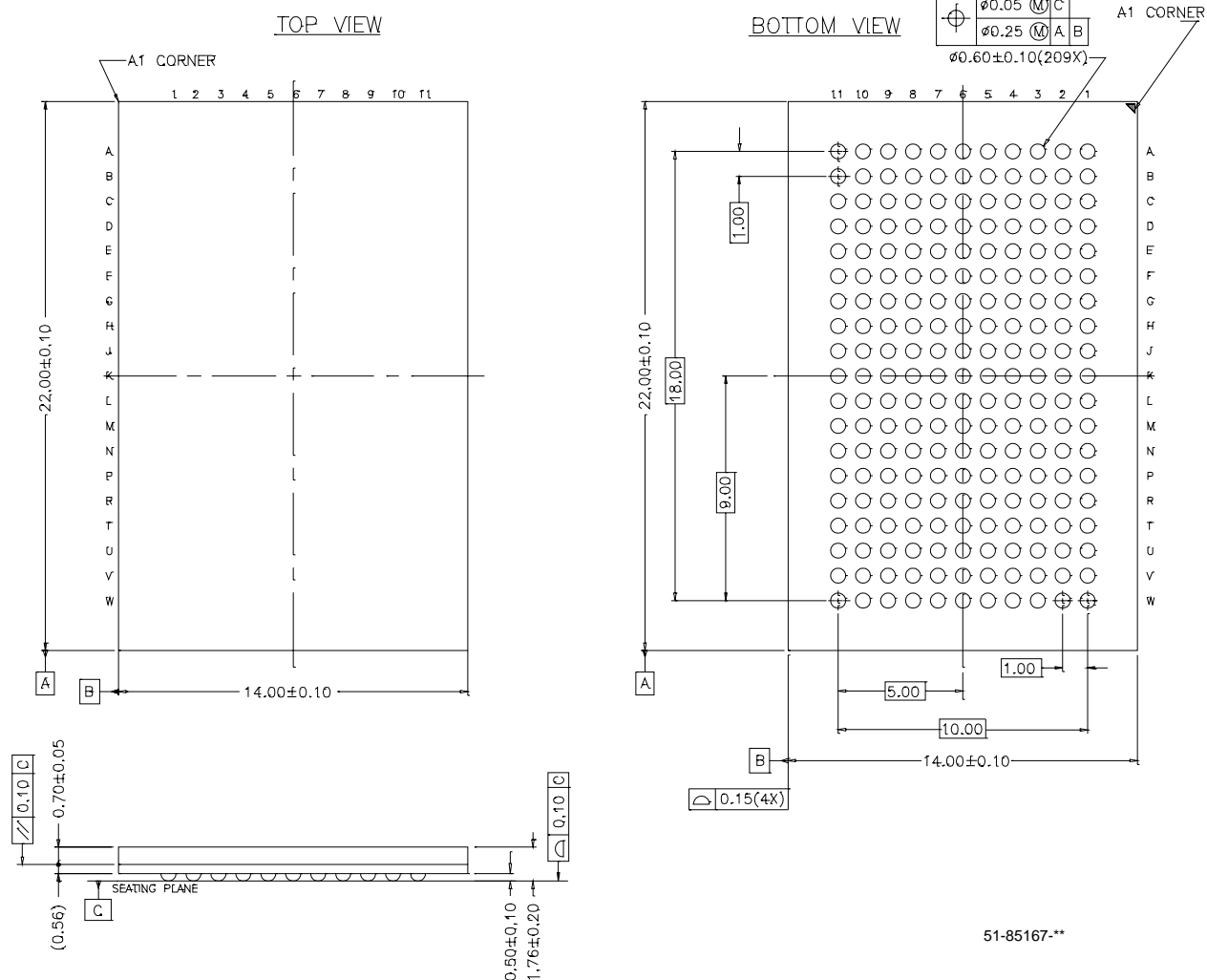
Package Diagrams (continued)

165-Ball FBGA (15 x 17 x 1.40 mm) BB165C



51-85165-A

Package Diagrams (continued)

209-Ball FBGA (14 x 22 x 1.76 mm) BB209A


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Document History Page

| Document Title: CY7C1471V25, CY7C1473V25 and CY7C1475V25, 72-Mbit (2M x 36/4M x 18/1M x 72) Flow-Through SRAM with NoBL™ Architecture Document Number: 38-05287 | | | | |
|--|----------------|-------------------|------------------------|--|
| REV. | ECN NO. | Issue Date | Orig. of Change | Description of Change |
| ** | 114674 | 08/06/02 | PKS | New Data Sheet |
| *A | 121522 | 01/27/03 | CJM | Updated features for package offering Updated ordering information Changed Advanced Information to Preliminary |
| *B | 223721 | See ECN | NJY | Changed timing diagrams Changed logic block diagrams Modified Functional Description Modified "Functional Overview" section Added boundary scan order for all packages Included thermal numbers and capacitance values for all packages Removed 150MHz speed grade offering Included ISB and IDD values Changed package outline for 165FBGA package and 209-ball BGA package Removed 119-BGA package offering |
| *C | 235012 | See ECN | RYQ | Minor Change: The data sheets do not match on the spec system and external web. |
| *D | 243572 | See ECN | NJY | Changed ball H2 from V_{DD} to NC in the 165-ball FBGA package in page 6 Changed ball R11 in 209-ball BGA package from DQPa to DQPe in page 7 Modified Capacitance values on page 21 |
| *E | 299511 | See ECN | SYT | Removed 117-MHz Speed Bin Changed Θ_{JA} from 16.8 to 24.63 °C/W and Θ_{JC} from 3.3 to 2.28 °C/W for 100 TQFP Package on Page # 22 Added lead-free information for 100-Pin TQFP, 165 FBGA and 209 BGA Packages Added comment of 'Lead-free BG packages availability' below the Ordering Information |